



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )

ELIYAHOU HARARI, ROBERT D. )  
NORMAN and SANJAY MEHROTRA )

Serial No.: 09/114,504 )

Filed: HEREWITH )

For: FLASH EEPROM SYSTEM )

San Francisco, California

Assistant Commissioner of Patents  
Washington, D.C. 20231

*J. Markley*  
*2-8-99*

*6/IDS*

**INFORMATION DISCLOSURE STATEMENT**

Sir:

The following Form 1449 and copies of each cited document are being filed herewith as an Information Disclosure Statement. Consideration of each of these documents by the Patent Examiner, and the making of each of them of record in the file of this application, are respectfully requested. The ten foreign patent documents are not in English; however it is believed that the concise statement of relevancy is met by the English abstract attached to the front of each document.

The required fee of \$240.00 is being filed herewith. The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment, to Deposit Account No. 13-1030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

Dated: 12/23/98 RECEIVED Vincent Yip  
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Atty. Docket: HARI.006USQ

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FORM PT01449  
(REV. 8-83)U.S. DEPARTMENT OF COMMERCE  
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## U. S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER							DATE	NAME	CLASS	SUB CLASS	FILING DATE
	A1	3	8	9	5	3	6	0	7/75	Cricchi et al.			
	A2	3	8	9	8	6	3	2	8/75	Spencer, Jr.			
	A3	3	9	0	6	4	5	5	9/75	Houston et al.			
	A4	3	9	1	4	7	5	0	10/75	Hadden, Jr.			
	A5	4	0	4	4	3	3	9	8/77	Berg			
	A6	4	0	5	8	7	9	9	11/77	George et al.			
	A7	4	0	6	4	4	0	5	12/77	Cricchi et al.			
	A8	4	1	1	5	8	5	0	9/78	Houston et al.			
	A9	4	1	3	0	8	9	0	12/78	Adam			
	A10	4	1	4	1	0	8	1	2/79	Horne et al.			
	A11	4	1	9	3	1	2	8	3/80	Brewer			

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUB CLASS	TRANS.? (YES/NO)
	B1	JP	58	0	8	6	7	7	7	1983	Japan		Abstract
	B2	JP	58	2	1	5	7	9	4	1983	Japan		Abstract
	B3	JP	58	2	1	5	7	9	5	1983	Japan		Yes
	B4	JP	59	1	6	2	6	9	5	1984	Japan		Abstract
	B5	JP	62	2	8	3	4	9	7	1987	Japan		Abstract

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, Etc.)

	C1	Flash Memory Cards, Oct. 1992, pp. 4-91, 4-95, and 4-96.											
	C2	Cricchi et al., "Nonvolatile Block-Oriented RAM", IEEE International Solid-State Circuits Conference, Feb, 13-15, 1974, Digest of Technical Papers.											
	C3	Brewer et al., "Block-Oriented Random Access MNOS Memory", National Computer Conference and Exposition, Chicago, May 6-10, 1974, AFIPS Conference Proceedings, vol 43. Pp. 837-840.											

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	A12	4	2	4	1	4	2	4		12/80	Dickson et al.			
	A13	4	4	1	2	3	0	9		10/83	Kuo			
	A14	4	4	2	8	0	4	7		1/84	Hayn et al.			
	A15	4	4	3	3	3	8	7		2/84	Dyer et al.			
	A16	4	5	2	7	2	5	7		7/85	Cricchi			
	A17	4	8	6	0	2	6	2		8/89	Chiu			
	A18	4	8	8	2	6	4	2		11/89	Tayler et al.			
	A19	4	8	8	7	2	3	4		12/89	Iijima			
	A20	4	9	2	0	4	7	8		4/90	Furuya et al.			
	A21	4	9	3	1	9	9	7		6/90	Mitsubishi et al.			
	A22	4	9	3	3	9	0	6		6/90	Terada et al.			

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER								DATE	COUNTRY	CLASS	SUB CLASS	TRANS.? (YES/NO)
	B6	JP	59	1	8	6	0	1	5	1984	Japan			Abstract
	B7	JP	62	2	8	3	4	9	6	1987	Japan			Yes
	B8	JP	63	1	8	3	7	0	0	1988	Japan			Abstract
	B9	JP	58	0	8	6	7	7	7	1983	Japan			Abstract
	B10	JP	52	0	0	8	7	3	8	1977	Japan			Abstract

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, Etc.)

C4	Brewer et al., Low Cost MNOS BORAM", Proceedings of IEEE National Aerospace Electronics Conference, NAECON '77, May 17-19, 1977.													
C5	Short, "Microprocessors and Programmed Logic", second edition. Ch 13.2.2 Electrically Erasable Programmable Read only Memory, EEPROM Prentice Hall International, 1987.													
C6	Fitzpatrick et al., "MNOS/SOS Memory Using High-Voltage Depletion-Mode CMOS Logic", Westinghouse Electric Corp., pp. 196-199.													
C7	SEEQ Technology Incorp., 48F512 512 Flash EEPROM, Preliminary Data Sheet, Oct 1988, pp. 2-1, 2-24.													

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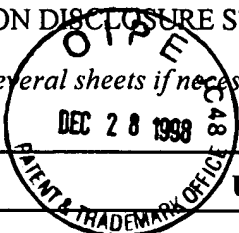
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	A23	4	9	4	9	3	0	9		8/90	Rao			
	A24	5	0	5	3	9	9	0		10/91	Kreifels et al.			
	A26	5	0	8	4	8	4	3		1/92	Mitsubishi et al.			
	A27	5	2	2	4	0	7	0		6/93	Fandrich et al.			
	A28	5	2	6	7	2	1	8		11/93	Elbert			
	A29	5	3	0	1	1	6	1		4/94	Landgraf et al.			
	A30	5	3	4	1	3	3	0		8/94	Wells et al.			
	A31	5	3	6	3	3	3	4		11/94	Alexander et al.			
	A32	5	4	1	8	7	5	2		5/95	Harari et al.			
	A33	5	6	4	8	9	2	9		7/97	Miyamoto			
	A34	5	7	1	9	8	0	8		2/98	Harari et al.			

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER								DATE	COUNTRY	CLASS	SUB CLASS	TRANS.? (YES/NO)
	B11	EP	0	2	8	3	2	3	8	1988	EPO			
	B12	JP	63	1	0	6	9	8	9	1988	Japan			Abstract
	B13	JP	63	2	2	5	9	9	9	1988	Japan			Abstract

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, Etc.)

	C8	Intel Corporation, 27F256 256K (32K x 8) CMOS Flash Memory", Data Sheet, May 1988, pp. 1-21.												
	C9	Cricchi et al., "The Drain-Source Protected MNOS Memory Device and Memory Endurance", IEDM Technical Digest, 1973, pp. 126-129.												
	C10	Cormier, "Erasable/Programmable Solid-State Memories", EDN, pp. 145-154, November 14, 1985, pp. 145-154.												

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	A35	4	5	2	1	8	5	3		6/85	Gutttag			
	A36	4	4	6	8	7	2	9		8/84	Schwartz			
	A37	4	9	3	9	6	9	0		7/90	Momodomi et al.			
	A38	4	9	5	3	1	2	9		8/90	Kobayashi et al.			
	A39	5	0	3	3	0	2	3		7/91	Hsia et al.			
	A40	4	8	6	0	2	2	8		8/89	Carroll			
	A41	4	8	1	1	2	9	3		3/89	Knothe et al.			
	A42	4	7	9	6	2	3	5		1/89	Sparks et al.			
	A43	4	7	5	8	9	8	8		7/88	Kuo			
	A44	4	7	5	8	9	8	6		7/88	Kuo			
	A45	4	6	8	5	0	8	4		8/87	Canepa			

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## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, Etc.)

	C11	Cernea et al., "A 1Mb Flash EEPROM", 1989 IEEE International Solid-State Circuits Conference.
	C12	Wilson, "1-Mbit Flash Memories seek their role in System Design", Computer Design, March 1, 1989, pp. 30 and 32.
	C13	Kynett et al., "An In-System Reprogrammable 32KX8 CMOS Flash Memory", IEEE J. Solid-State Circuits, vol. 23, No. 5, October 1988, pp. 1157-1163.

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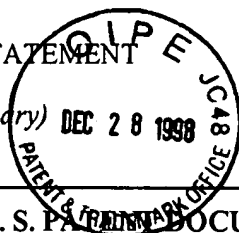
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	A57	4	8	4	1	4	8	2		6/89	Kreifels et al.			

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